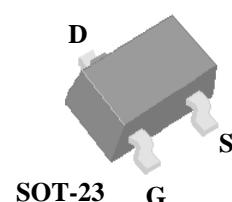




- ▼ Simple Drive Requirement
- ▼ Small Package Outline
- ▼ Surface Mount Device
- ▼ RoHS Compliant & Halogen-Free

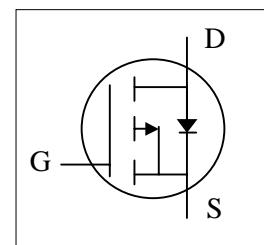


BV_{DSS}	-100V
$R_{DS(ON)}$	0.5Ω
I_D	- 1.2A

Description

AP10P500 series are from Advanced Power innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The special design SOT-23 package with good thermal performance is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.



Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Drain Current ³ , $V_{GS} @ 10\text{V}$	-1.2	A
$I_D @ T_A=70^\circ\text{C}$	Drain Current ³ , $V_{GS} @ 10\text{V}$	-0.95	A
I_{DM}	Pulsed Drain Current ¹	-4.8	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation	1.38	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Maximum Thermal Resistance, Junction-ambient ³	90	°C/W



Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-100	-	-	V
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	-	-	0.5	Ω
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-0.5\text{A}$	-	-	0.6	Ω
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-	-3	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	-	3.3	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=-80\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-25	μA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_{\text{D}}=-1\text{A}$	-	10.5	17	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=-50\text{V}$	-	1.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge		-	2.5	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DS}}=-50\text{V}$	-	7	-	ns
t_r	Rise Time	$I_{\text{D}}=-1\text{A}$	-	5	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	17	-	ns
t_f	Fall Time		-	5	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	420	670	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=-50\text{V}$	-	35	-	pF
C_{rss}	Reverse Transfer Capacitance		f=1.0MHz	-	25	-

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=-1\text{A}, V_{\text{GS}}=0\text{V}$	-	-	-1.3	V
t_{rr}	Reverse Recovery Time	$I_{\text{S}}=-1\text{A}, V_{\text{GS}}=0\text{V},$ $dI/dt=100\text{A}/\mu\text{s}$	-	37	-	ns
Q_{rr}	Reverse Recovery Charge		-	27	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board ; 270°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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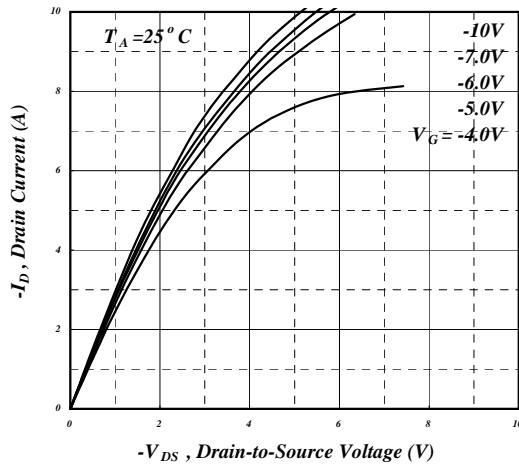


Fig 1. Typical Output Characteristics

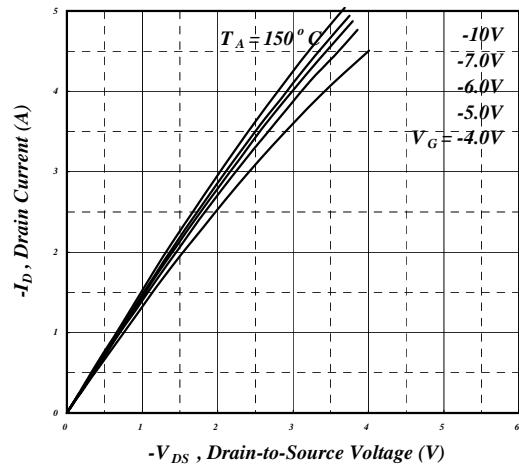


Fig 2. Typical Output Characteristics

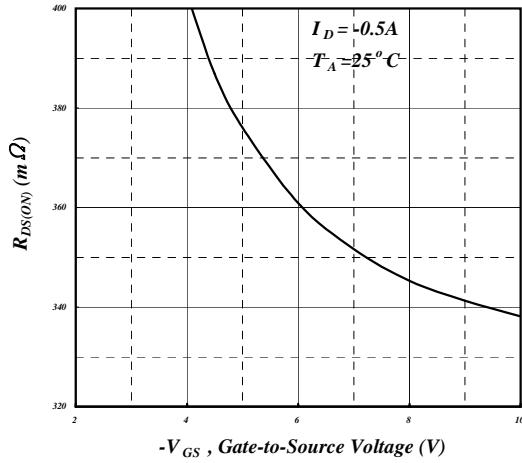


Fig 3. On-Resistance v.s. Gate Voltage

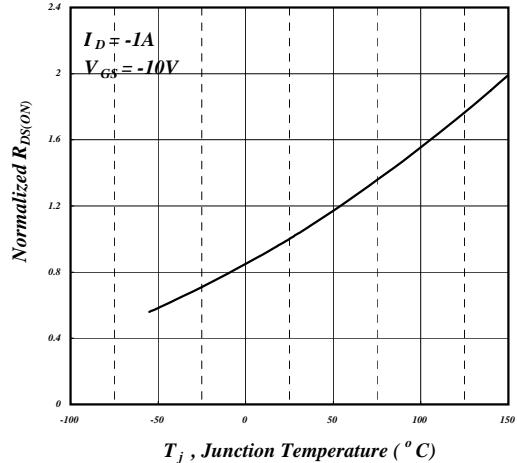


Fig 4. Normalized On-Resistance v.s. Junction Temperature

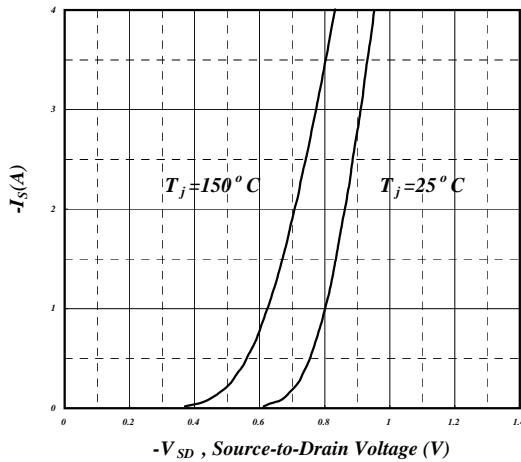


Fig 5. Forward Characteristic of Reverse Diode

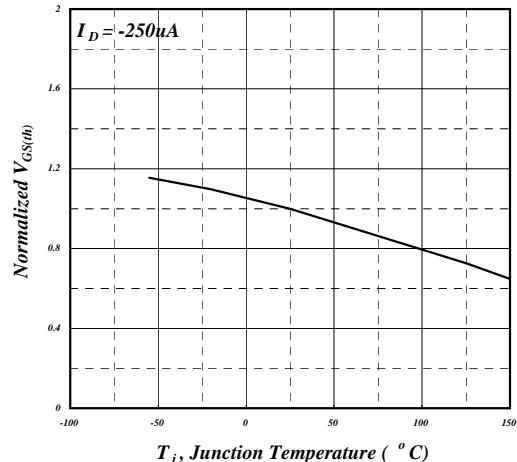


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

AP10P500N

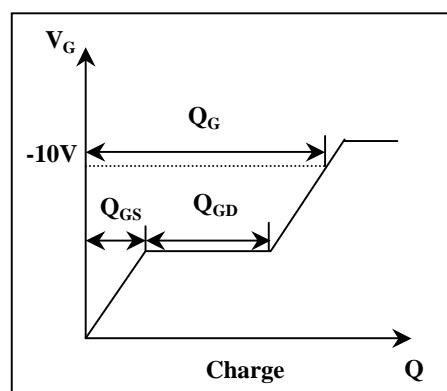
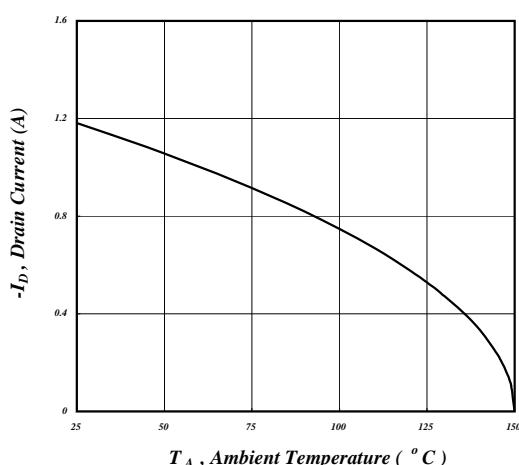
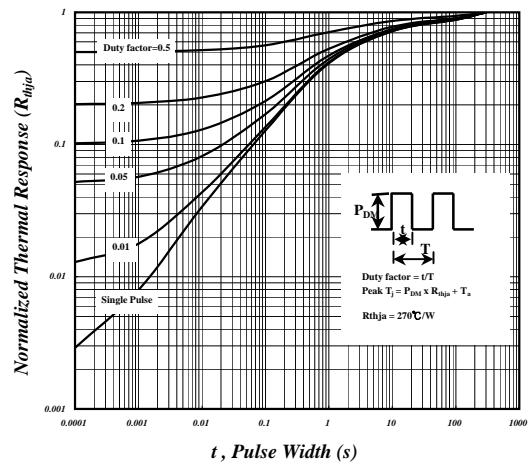
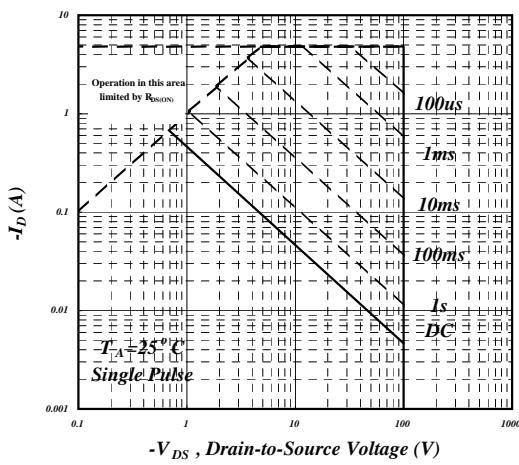
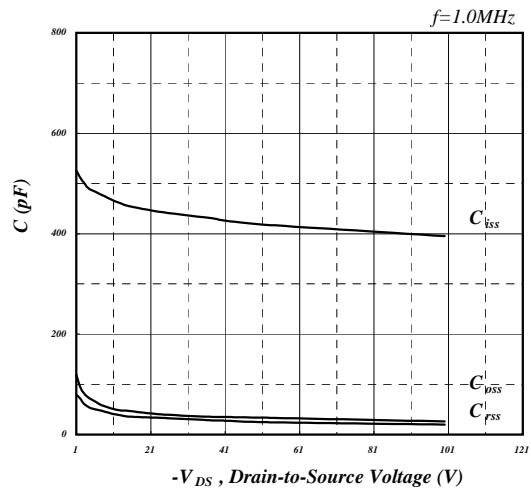
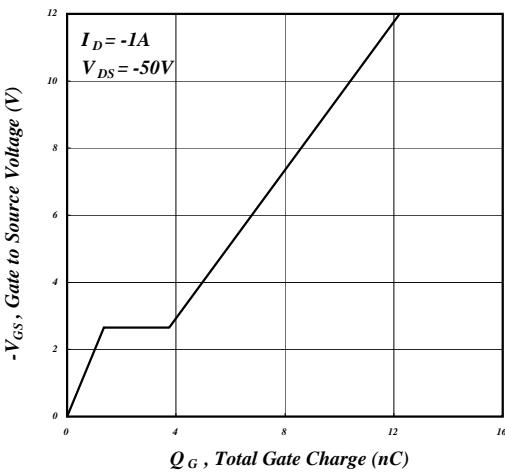


Fig 11. Drain Current v.s. Ambient Temperature

Fig 12. Gate Charge Waveform

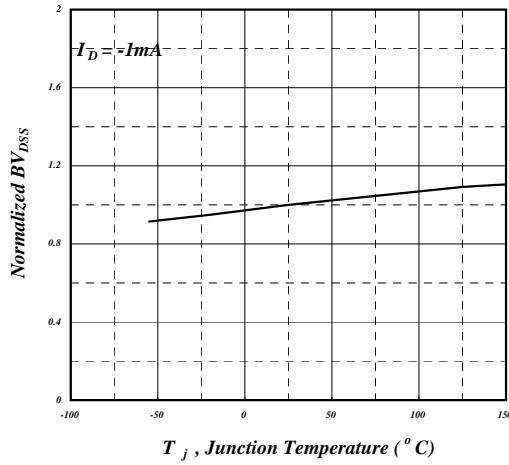


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

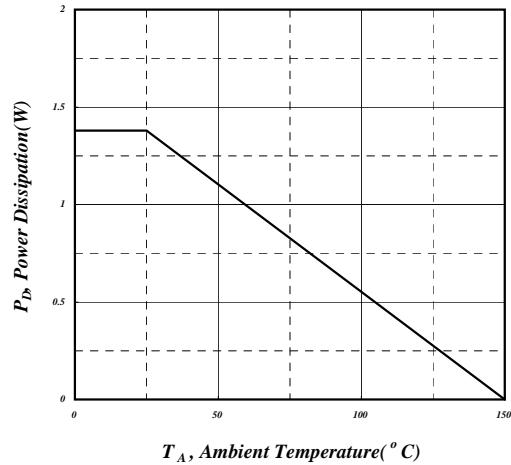


Fig 14. Total Power Dissipation

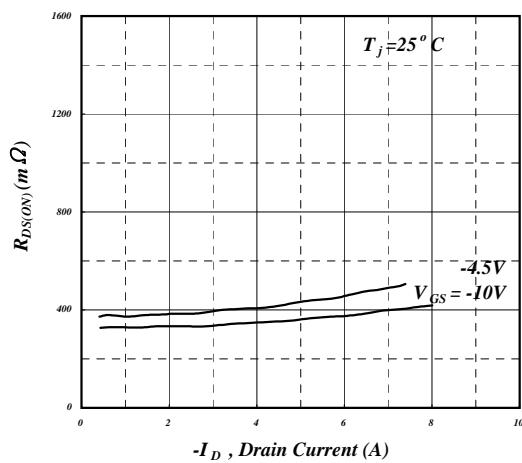


Fig 15. Typ. Drain-Source on State Resistance

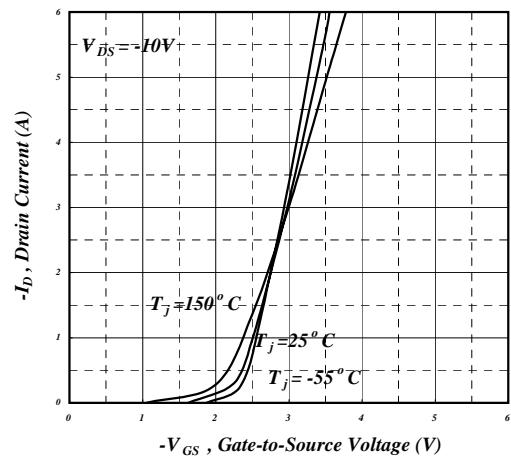
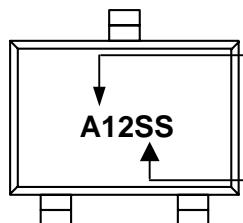


Fig 16. Transfer Characteristics



AP10P500N

MARKING INFORMATION



Part Number : A12

Date Code : SS

SS:2004,2008,2012,2016,2020...

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